

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

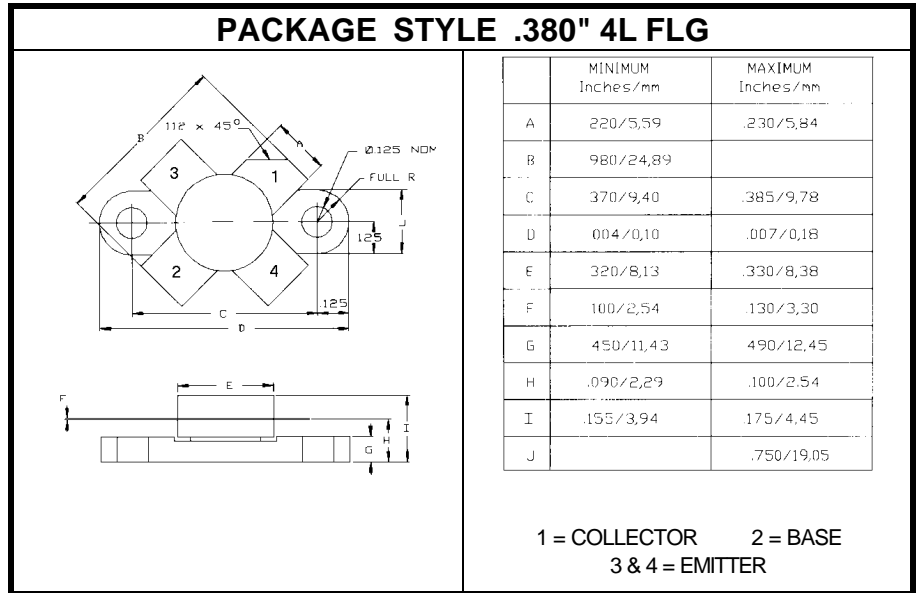
The **ASI S15-28** is Designed for Class AB or C, Common Emitter Linear HF Communications Applications.

**FEATURES INCLUDE:**

- High Power Gain
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	3.0 A
<b>V<sub>CB</sub></b>	65 V
<b>P<sub>DISS</sub></b>	30 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +200 °C
<b>q<sub>JC</sub></b>	5.8 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 200 mA	65			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 200 mA	35			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 30 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 200 mA	10			<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 30 V      f = 1.0 MHz			35	<b>pF</b>
<b>P<sub>out</sub></b>	V <sub>CE</sub> = 28 V      P <sub>in</sub> = 500 mW      fo = 30 MHz	15	---		<b>W</b>
<b>P<sub>g</sub></b>		15	18	---	<b>dB</b>
<b>h<sub>c</sub></b>		---	65		<b>%</b>